

STRAINED SILICON MOSFETS HAVING NMOS GATES WITH WORK FUNCTIONS
FOR COMPENSATING NMOS THRESHOLD VOLTAGE SHIFT

Inventors: Ihsan J. Djomehri et al. - Attorney: Ronald Coslick - 039153-0688

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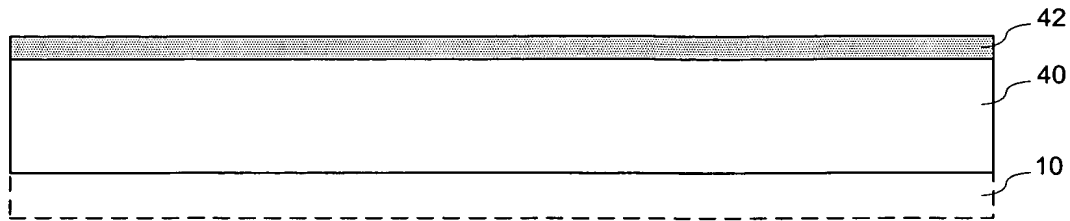


Figure 4a

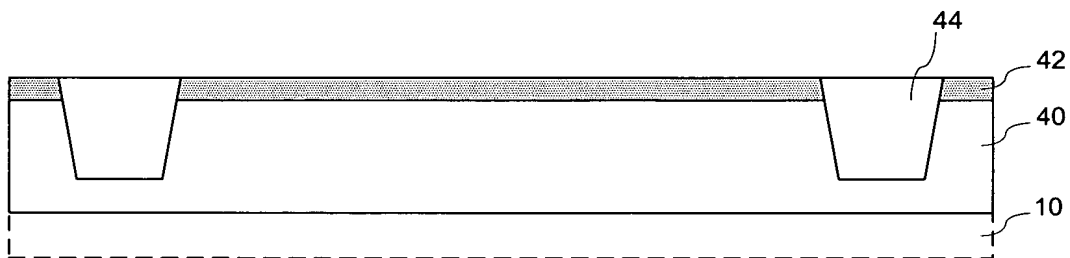


Figure 4b

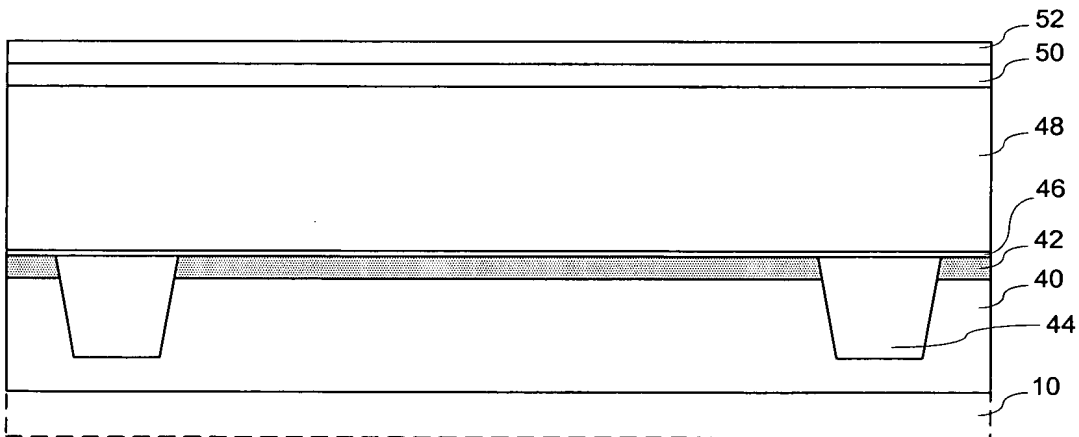


Figure 4c

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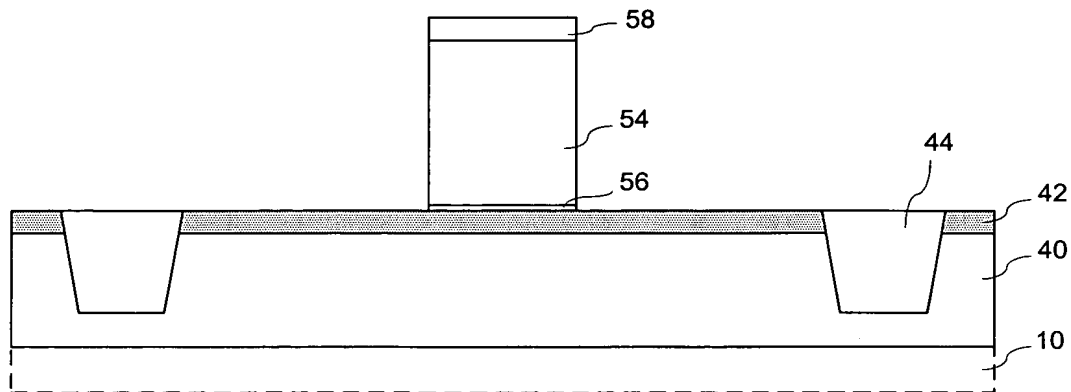


Figure 4d

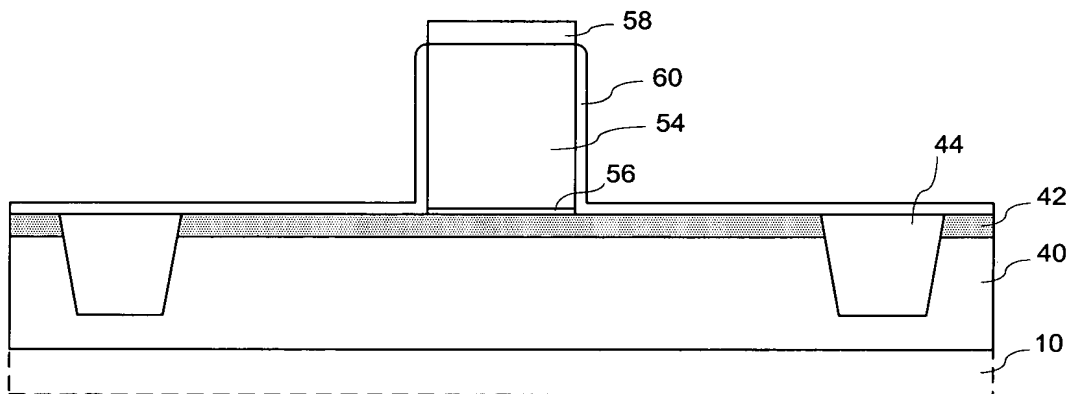


Figure 4e

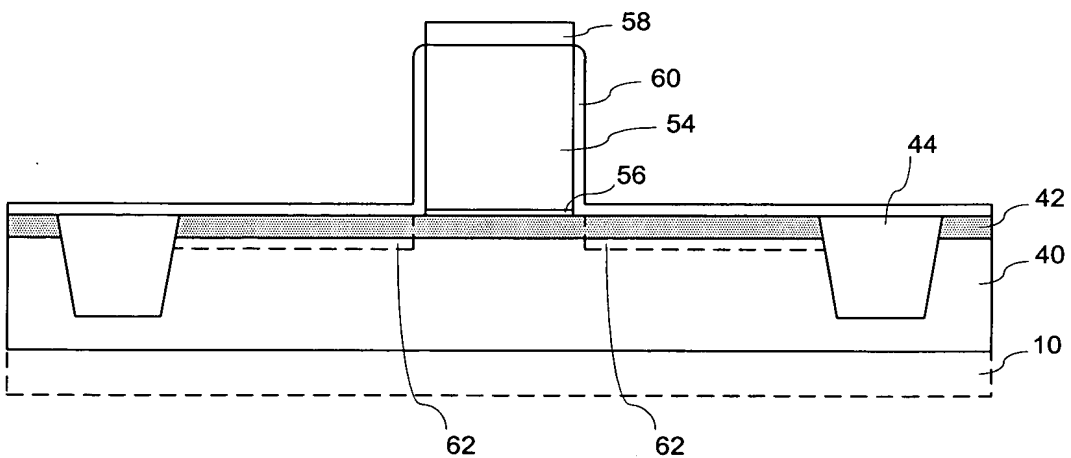


Figure 4f

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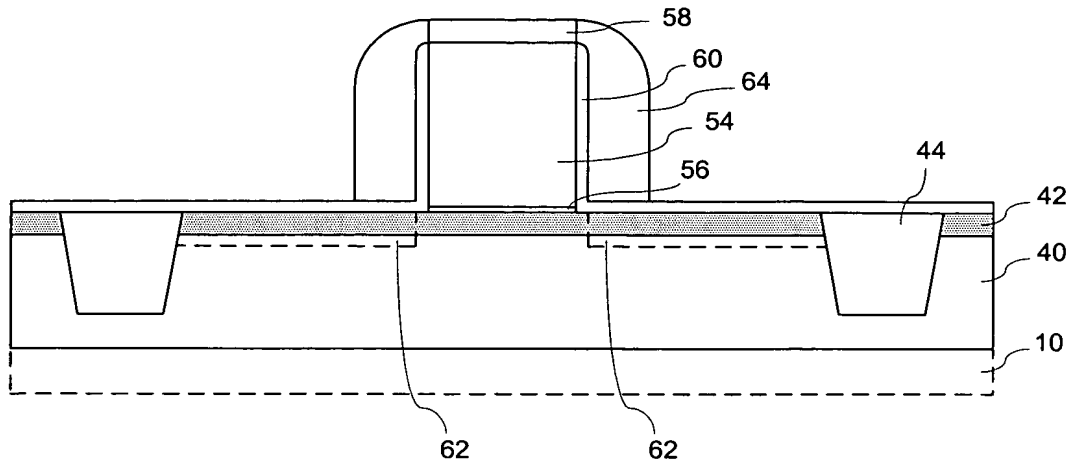


Figure 4g

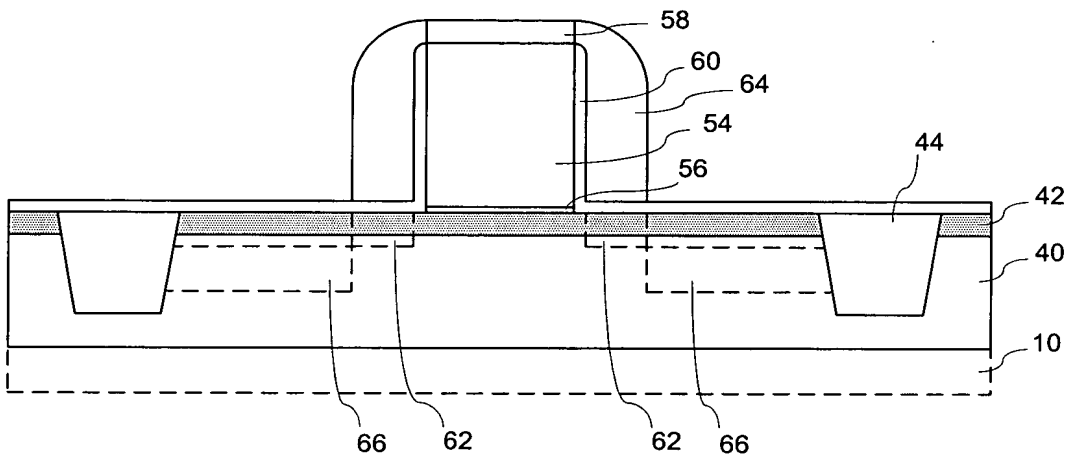


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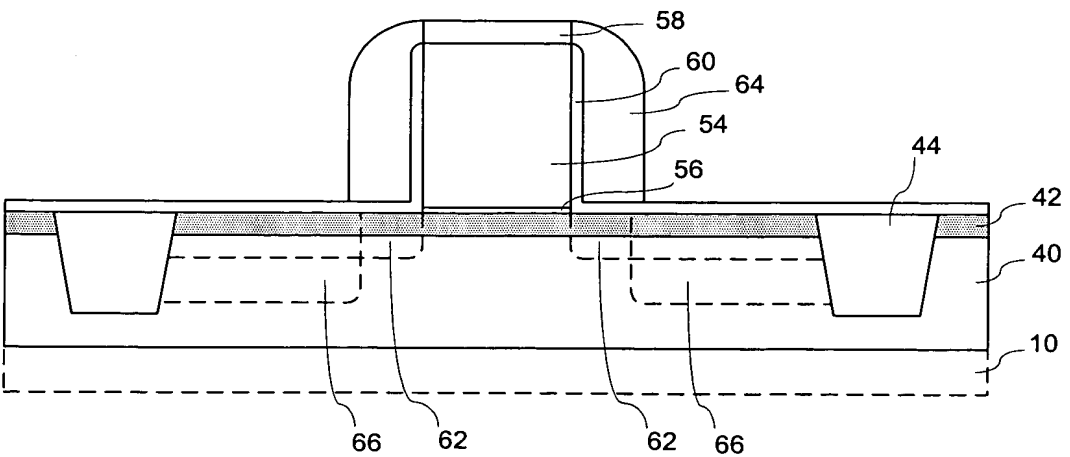


Figure 4i

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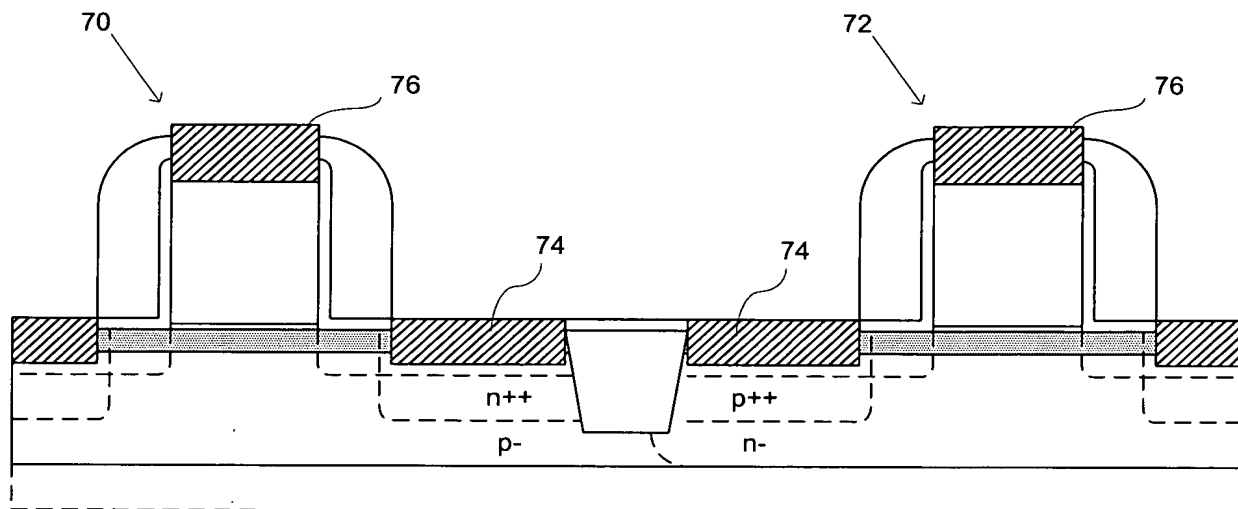


Figure 5a

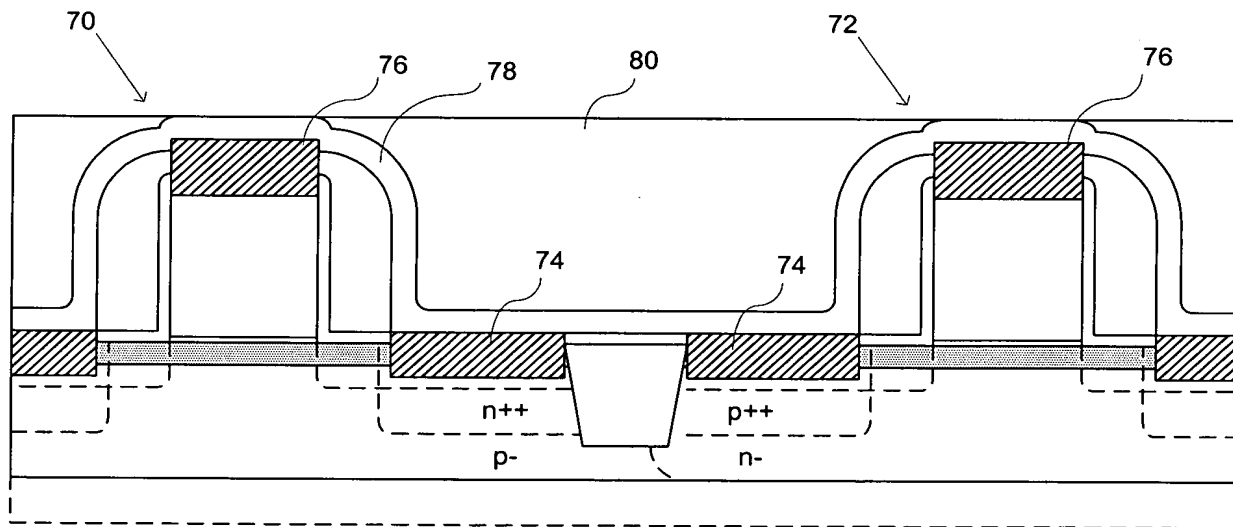


Figure 5b

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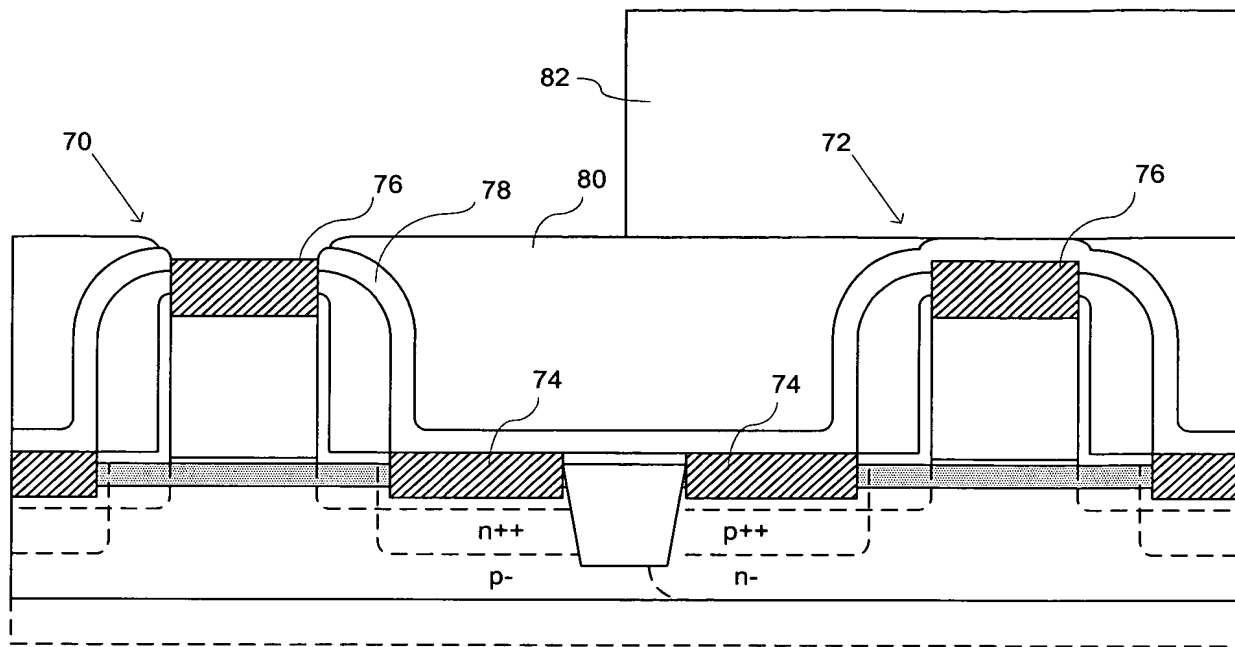


Figure 5c

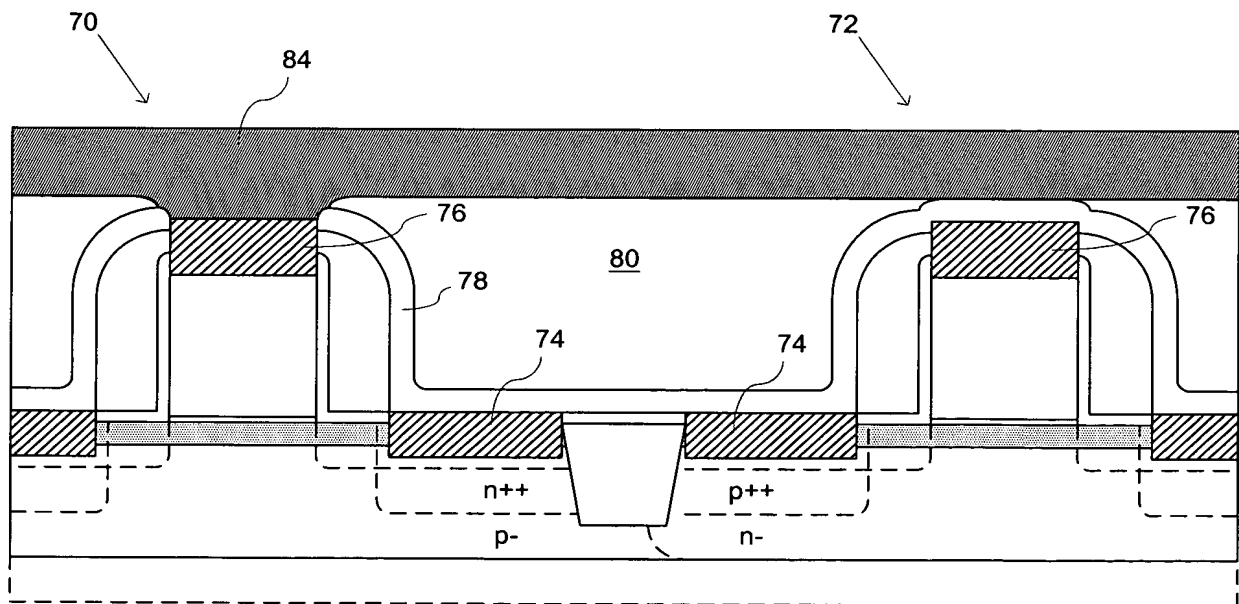


Figure 5d



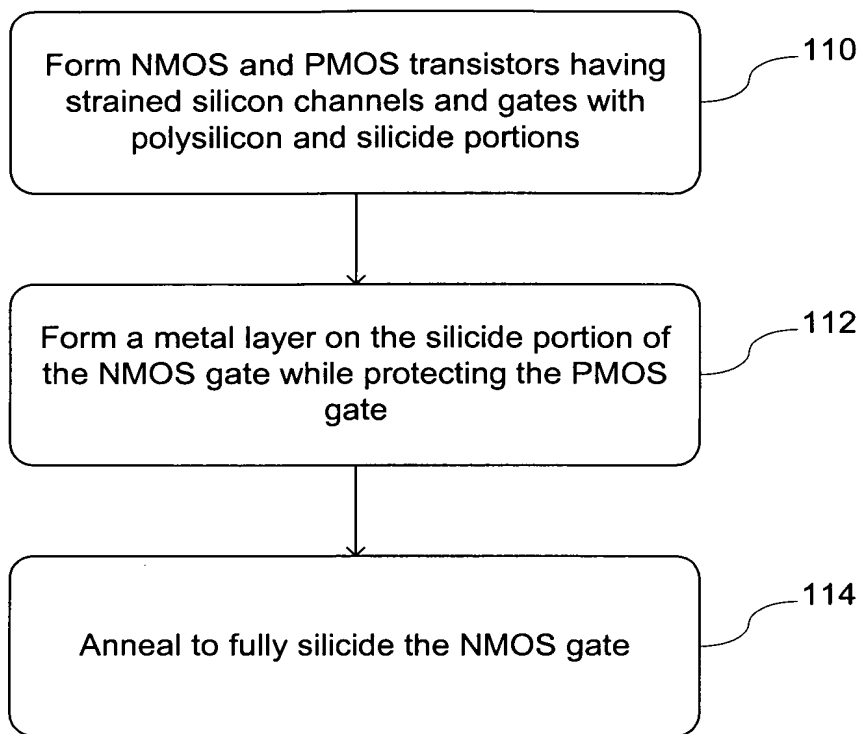


Figure 6

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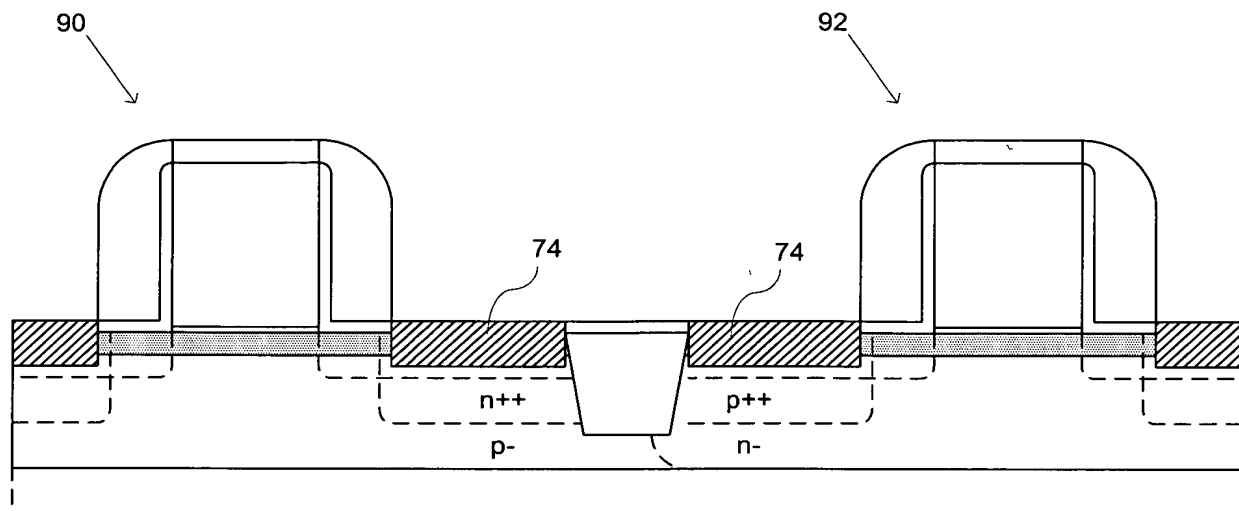


Figure 7a

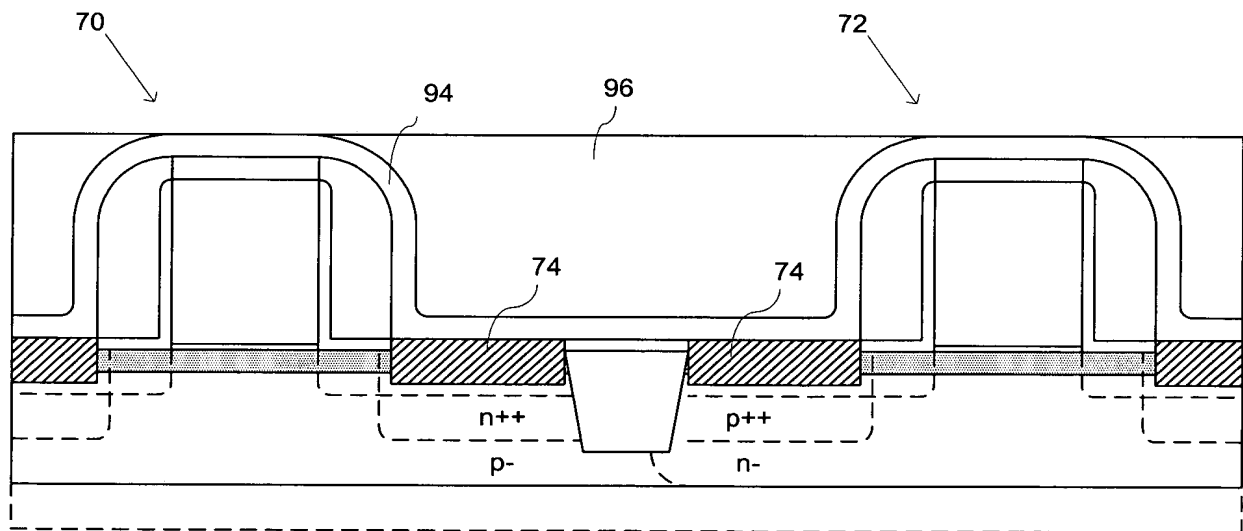


Figure 7b

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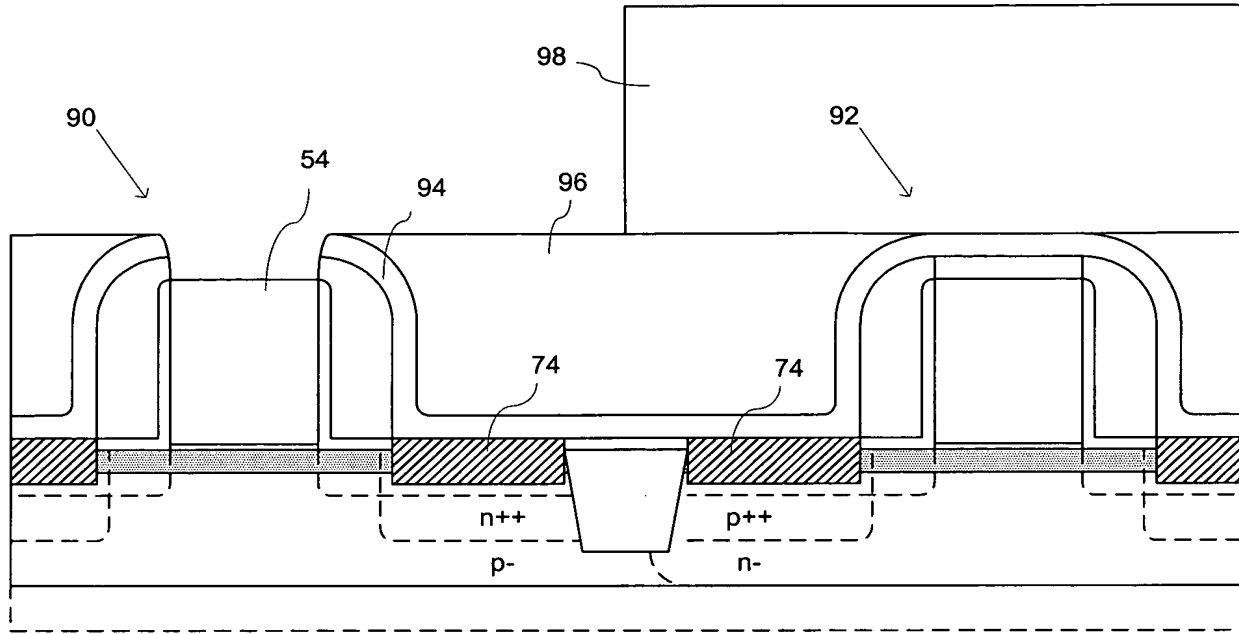


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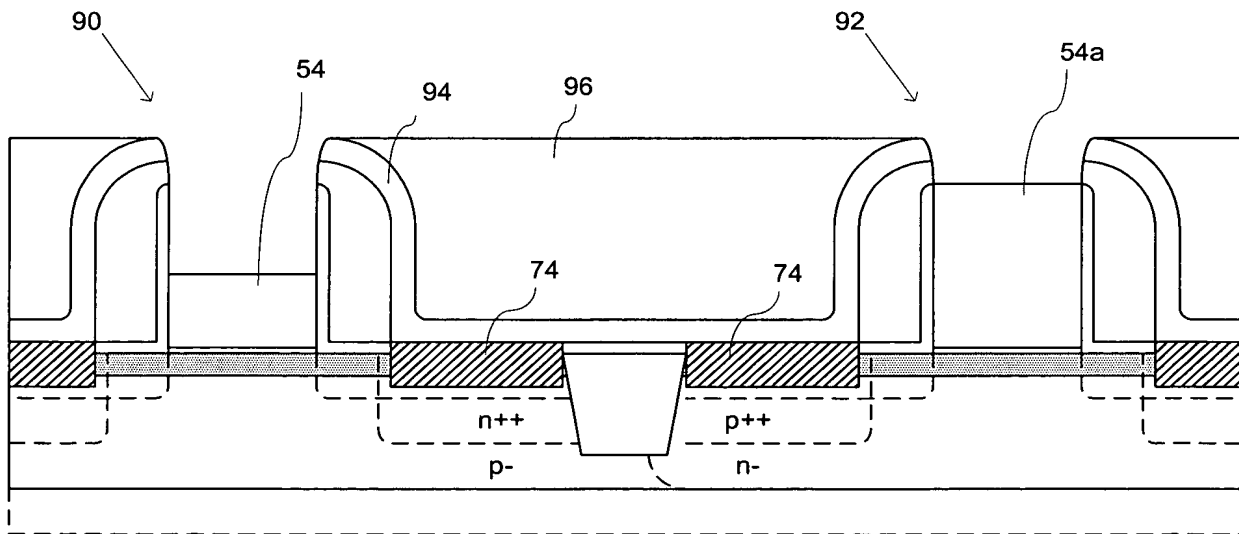


Figure 7d

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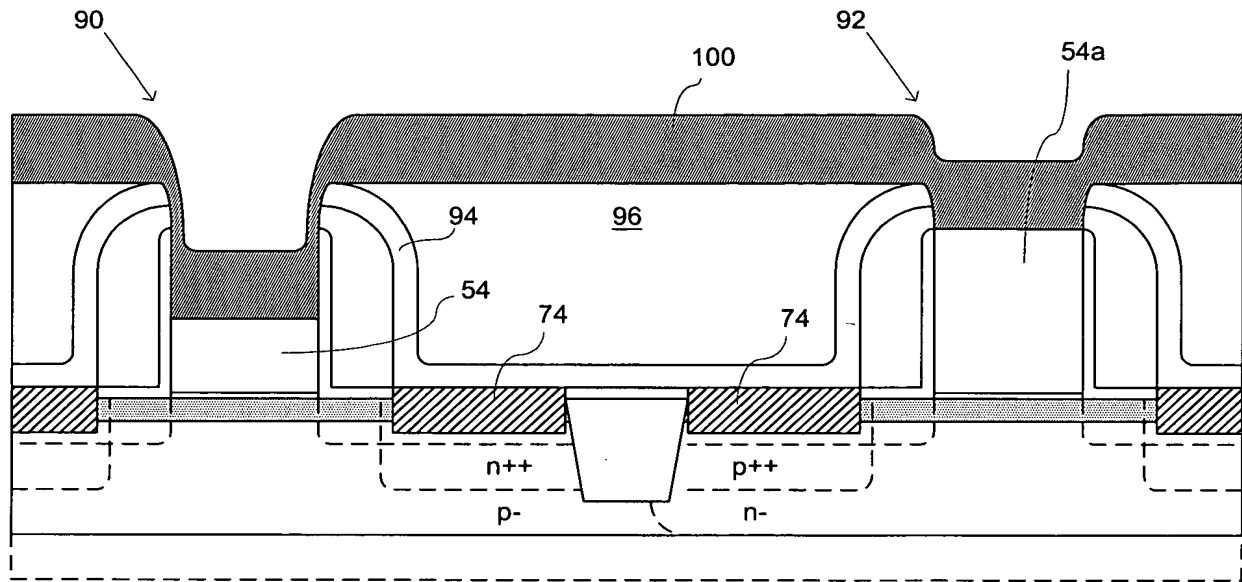


Figure 7e

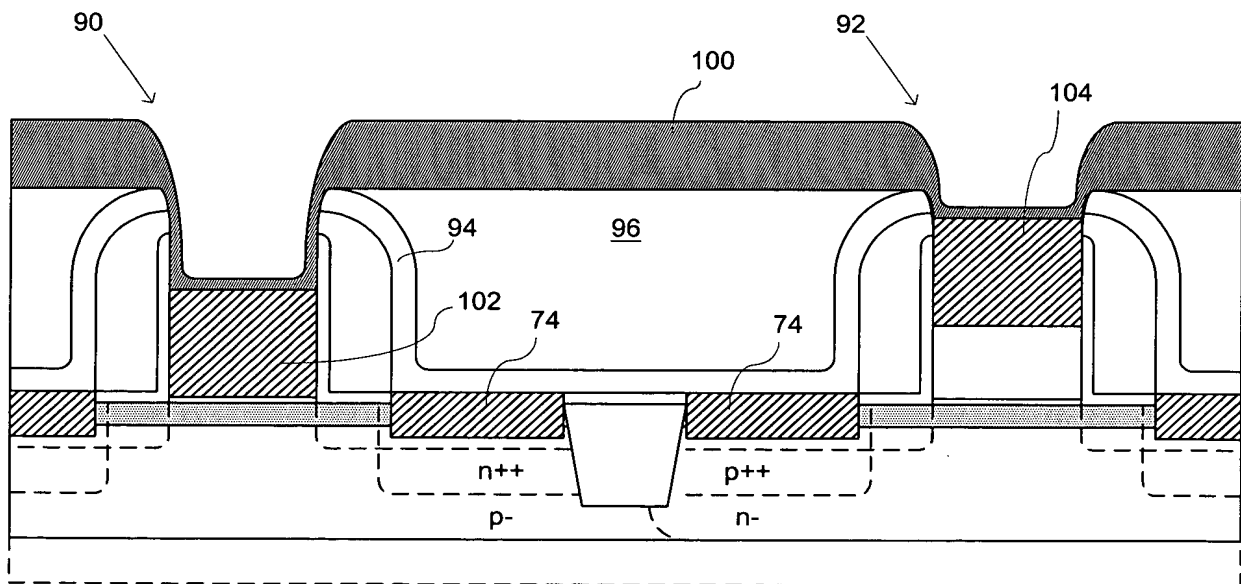


Figure 7f

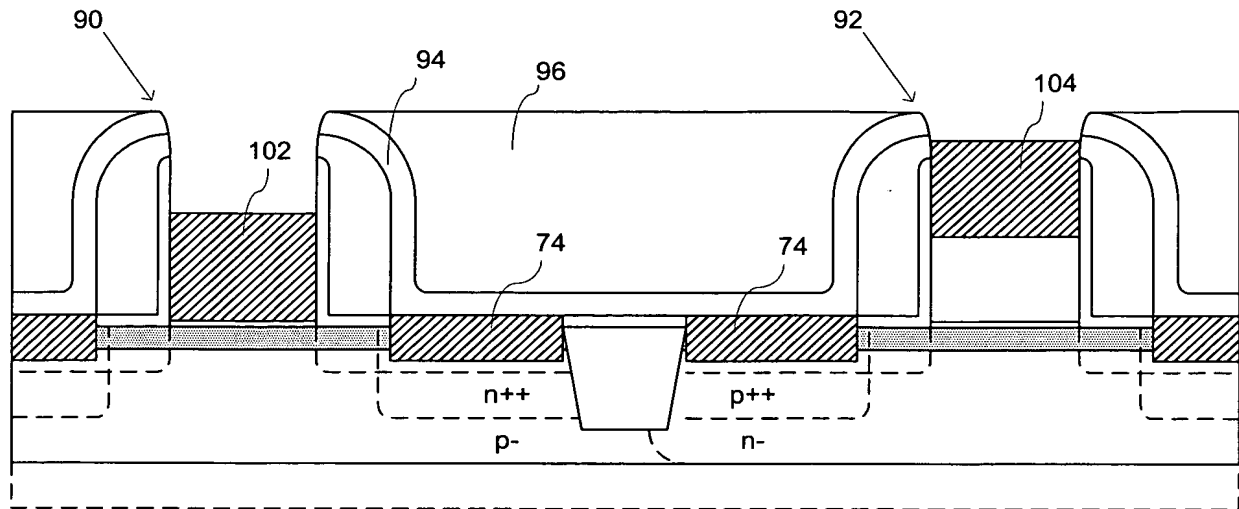


Figure 7g

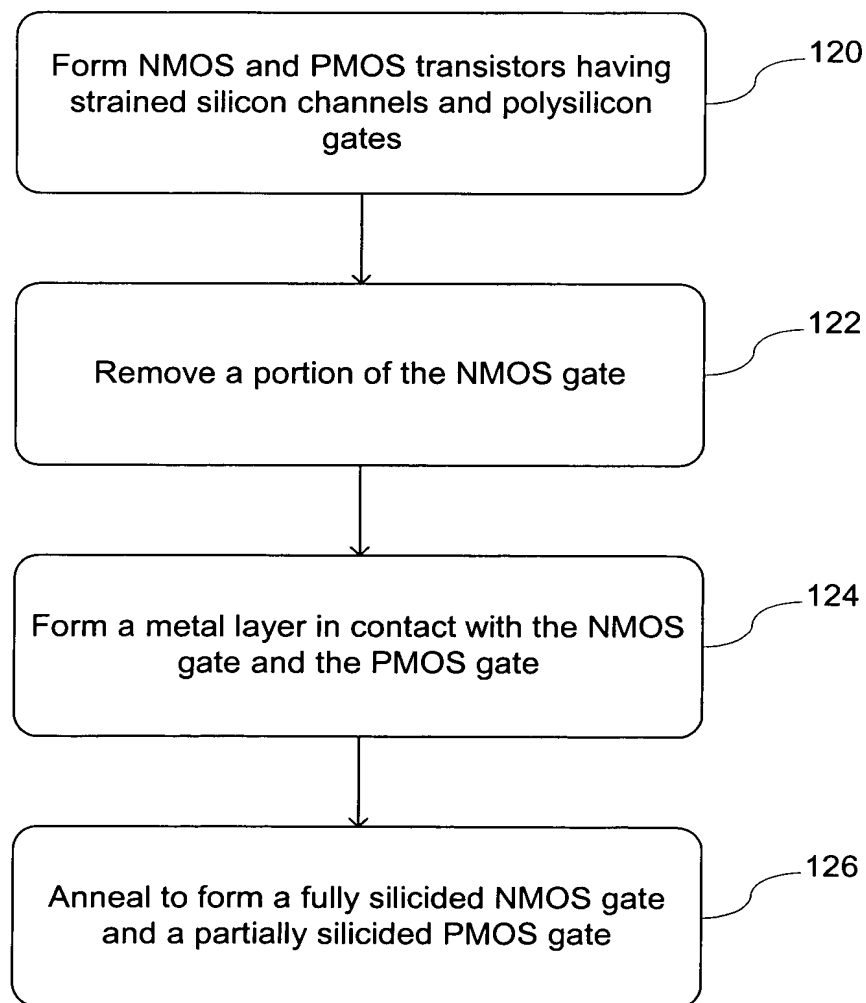


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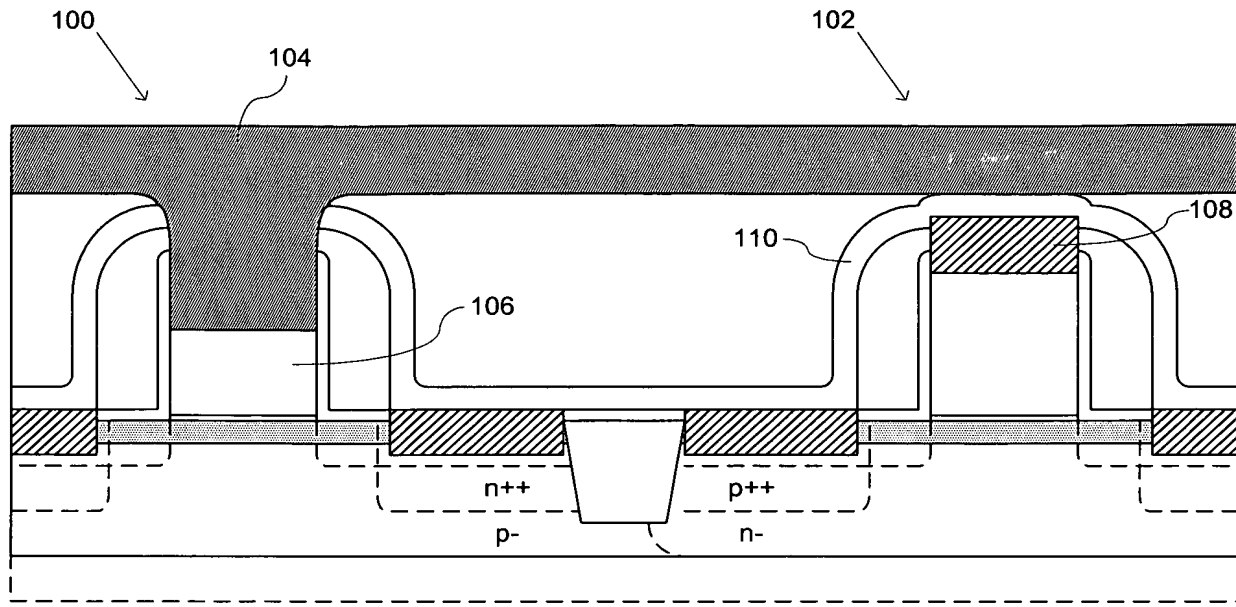


Figure 9

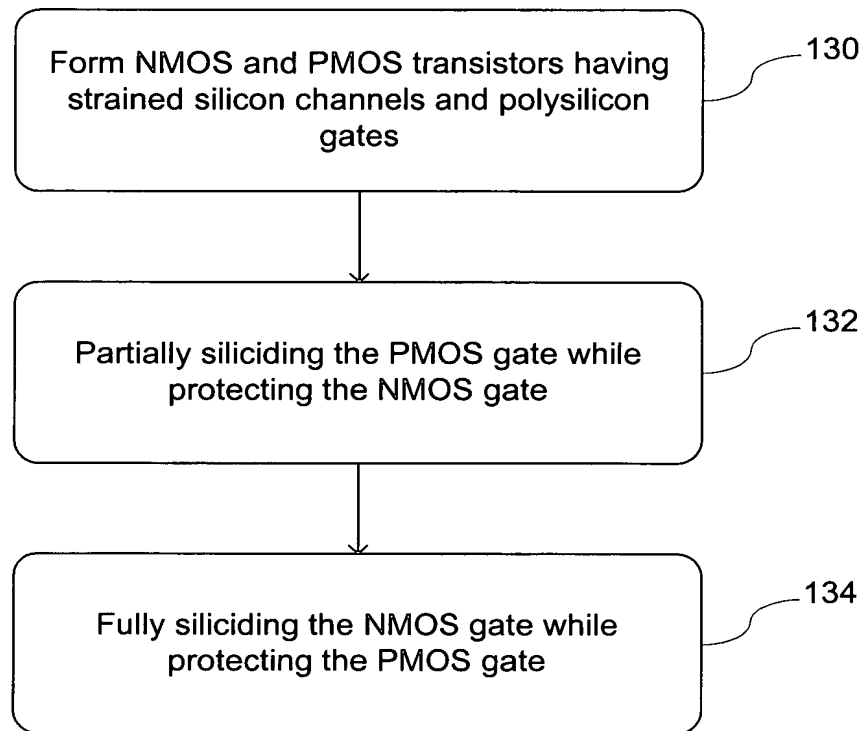


Figure 10